

Time-dependent electron driven tunneling phenomena for multipurpose terahertz applications:

Self consistent computation of conduction and displacement current in mesoscopic systems

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Outline

1. Theoretical development:

1.1.- Introduction:

1.1.1- From macroelectronic to nanoelectronic. THZ Gap

1.1.2- Total (conduction plus displacement) current conservation

1.2- Time-dependent self-consistent solution of the Poisson and many-particle Schrödinger equations:

1.2.1- Quantum trajectories with electron-electron interaction

1.2.2.- Current in terms of the Ramo-Shockley theorem.

2. THz applications:

2.1.- Driven Tunneling Devices (DTD)

2.2.- Numerical DTD results:

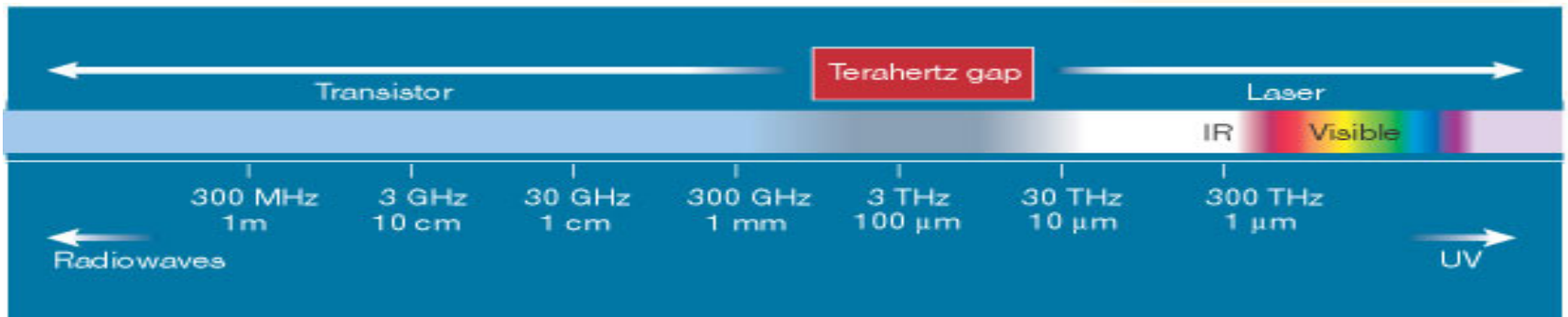
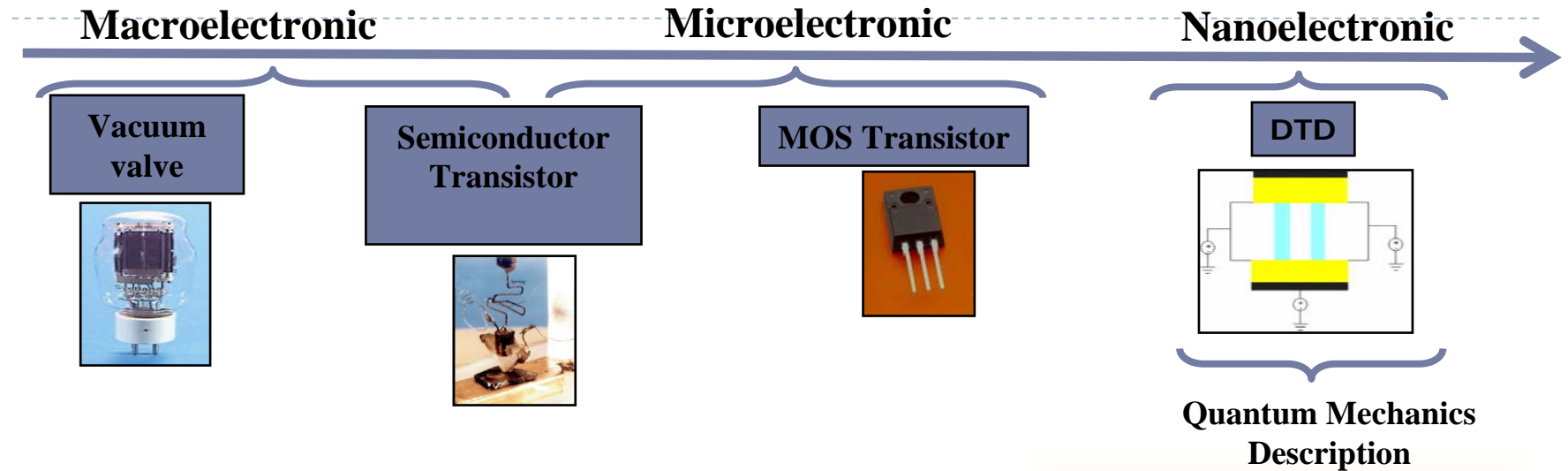
2.2.1.- Rectifier

2.2.2.- Harmonic Generator

3.- Conclusions



1.1.- From macroelectronic to nanoelectronic. THZ Gap



Goal → Quantum electrons transport at THz frequencies → Time-dependent many-particle Schrödinger equation

1.2.-Total (conduction + displacement) current conservation

➔ Total current in high frequency electron devices:

$$J_T(r,t) = \underbrace{J_c(r,t)}_{\text{Conduction}} + \underbrace{\epsilon(r) \frac{\partial E(r,t)}{\partial t}}_{\text{Displacement}}$$

[Ya. M. Blanter and M. Büttiker, Phys. Rep. (2000)]

1. $\nabla(\epsilon(r)E(r,t)) = \rho(r,t)$ ← 1st Maxwell (Poisson) equation
(electron-electron interaction)

2. Many-particle Schrödinger equation

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2.1.- Quantum trajectories with electron-electron interaction

The problem...

► Many-particle (Coulomb interaction) Schrödinger equation

$$\Phi(\vec{r}_1, \dots, \vec{r}_N, t) \quad \text{Many particle wave function}$$
$$i\hbar \frac{\partial \Phi(\vec{r}_1, \dots, \vec{r}_N, t)}{\partial t} = \left\{ \sum_{k=1}^N -\frac{\hbar^2}{2m} \nabla_{\vec{r}_k}^2 + U(\vec{r}_1, \dots, \vec{r}_N, t) \right\} \Phi(\vec{r}_1, \dots, \vec{r}_N, t)$$

Practical solution is inaccessible for more than very few electrons

Numerical viability 1 eq N-Dim: N=100 electrons, L=100nm length (with $\Delta x=0.1$ nm)

n° of variables = $1000^{3N} = 1000^{300}$ variables !!!!!!!!!!!!!!!

The solution...

Electron-electron approximations in the literature:

- Fermi liquid (no Coulomb interaction)
- Perturbative (Green-function) treatment
- Density Functional theory

2.1.- Quantum trajectories with electron-electron interaction

The solution...

[D. Bohm, Phys. Rev, 1952]

- ▶ New approximation to simplifying the evaluation of many-particle Schrödinger equation.



$$i\hbar \frac{\partial \Psi_a(\vec{r}_a, t)}{\partial t} = \left\{ -\frac{\hbar^2}{2 \cdot m} \nabla_{\vec{r}_a}^2 + U_a(\vec{r}_a, \vec{R}_a[t], t) + G_a(\vec{r}_a, \vec{R}_a[t], t) + i \cdot J_a(\vec{r}_a, \vec{R}_a[t], t) \right\} \Psi_a(\vec{r}_a, t)$$

[X.Oriols, Phs. Rev. Letters, 2007]

Numerical viability N-eqs 1-Dim: N=100 electrons, L=100nm length (with $\Delta x=0.1$ nm)

n° of variables = $3 \cdot 1000 \cdot N = 300\,000$ variables

The self-consistent coupling between the electron dynamics obtained from the last equation and the Coulomb potential (obtained from 3D Poisson solver) is achieved by using Bohm trajectories.

2.2.- Current in terms of the Ramo-Shockley theorem

➔ Ramo-Shockley theorem with Bohm trajectories in volume Ω and total surface S

$$I_i(t) = \Gamma_i^q(t) + \Gamma_i^e(t) + \cancel{\Gamma_i^m(t)}$$

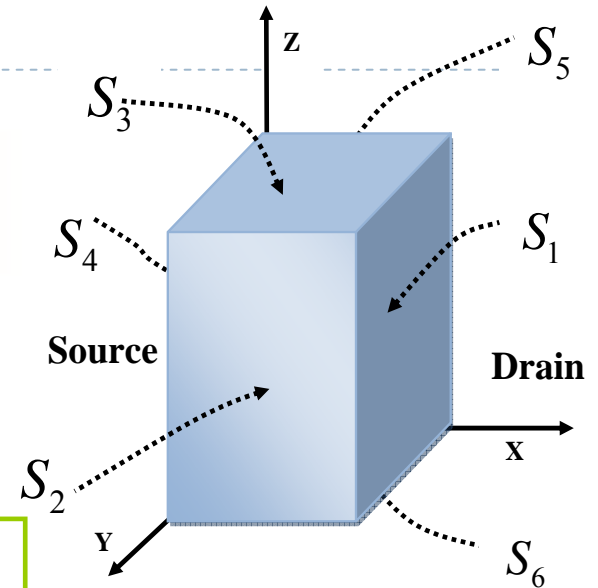
$$\Gamma_i^q(t) = - \int_{\Omega} F_i(r) \cdot J_c(r, t) \cdot d^3 r$$

Conduction current density

$$\Gamma_i^e(t) = \int_S F_i(r) \cdot \epsilon(r) \cdot \frac{\partial V(r, t)}{\partial t} \cdot ds$$

Potential scalar

$$\cancel{\Gamma_i^m(t) = \int_{\Omega} F_i(r) \cdot \epsilon(r) \cdot \frac{\partial^2 A(r, t)}{\partial t^2} \cdot d^3 r}$$



$$\vec{F}(\vec{r}) = -\nabla\Phi(\vec{r})$$

$$\nabla(\epsilon(\vec{r}) \cdot \vec{F}(\vec{r})) = -\nabla(\epsilon(\vec{r}) \cdot \nabla\Phi(\vec{r})) = 0$$

$$\Phi(\vec{r}) = 1 ; \vec{r} \in S_i$$

$$\Phi(\vec{r}) = 0 ; \vec{r} \in S_{h \neq i}$$

[X.Oriols, A.Alarcon, et al. *Phy. Rev. B*, 2005]

[A.Alarcon, X.Oriols, et al. *JSTAT*, 2008 (Submitted)]

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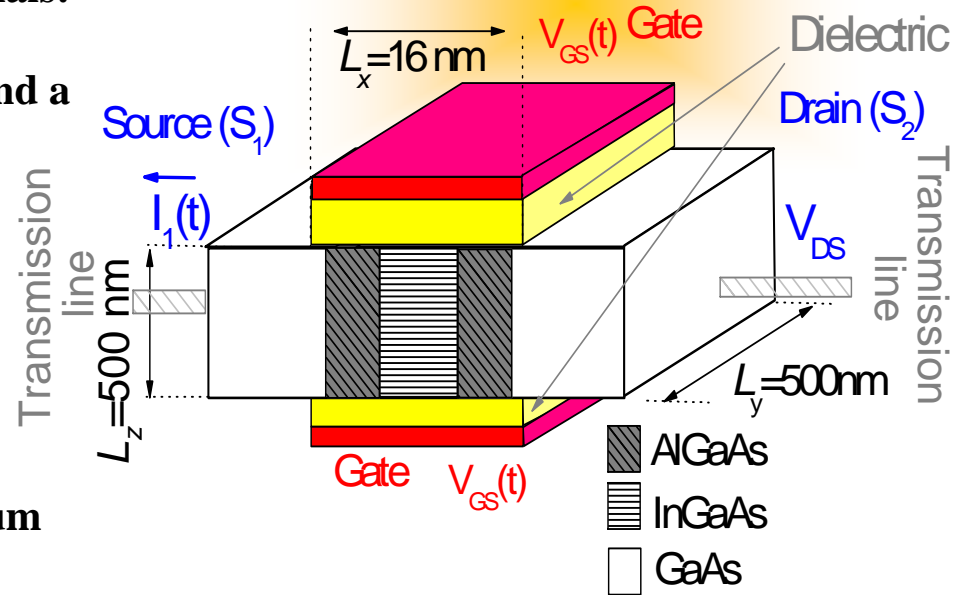
3.- Driven Tunneling Devices (DTD)

▶ DTD geometry

- ▶ Field effect transistor with three terminals: double gate, drain and source. Inside active region, a double barrier and a quantum well

▶ DTD operation

- ▶ The output current (from a source to the drain) is controlled by the gate voltage.
- ▶ Coupling non-stationary (THz) quantum transport with electromagnetism.
- ▶ The density of states inside the active region is designed “by hand” (modifying the structure geometry).



[DTD was patented in the year 2005]

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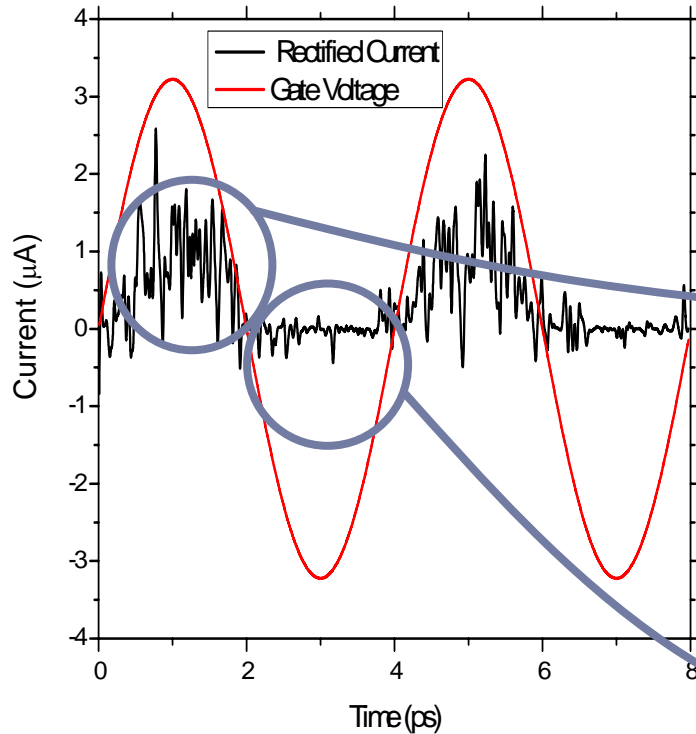
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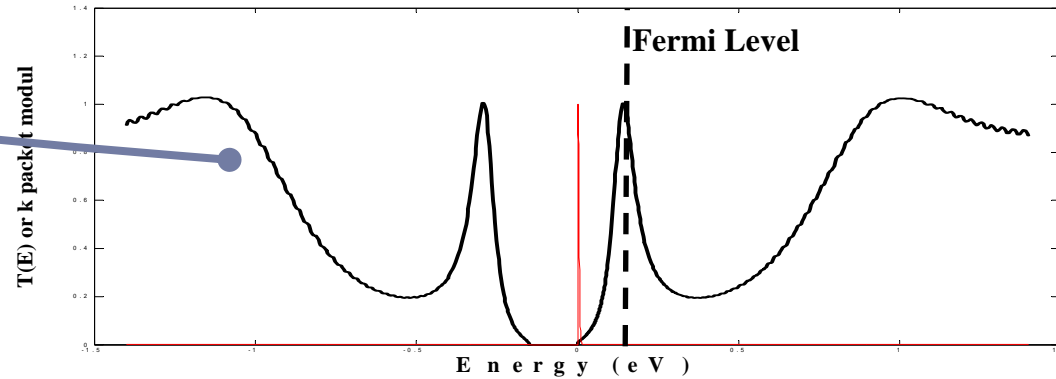
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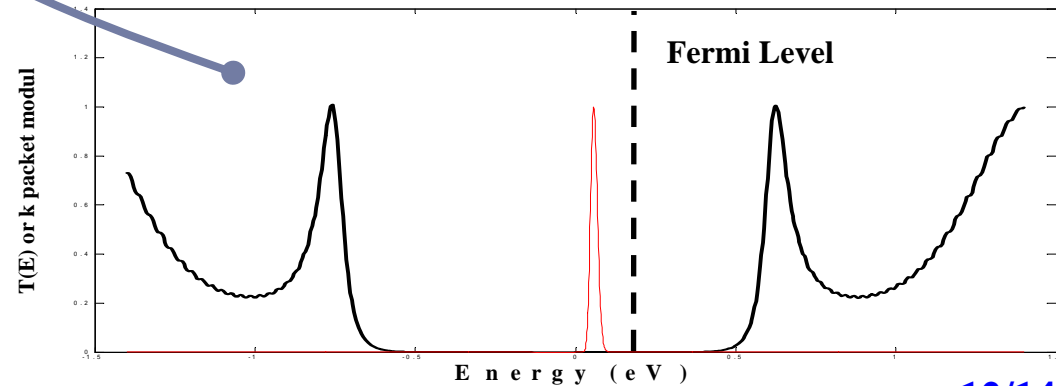
4.1.- DTD Applications: THz Rectifier



“Qualitative” explanation “ON”:



“Qualitative” explanation “OFF”:



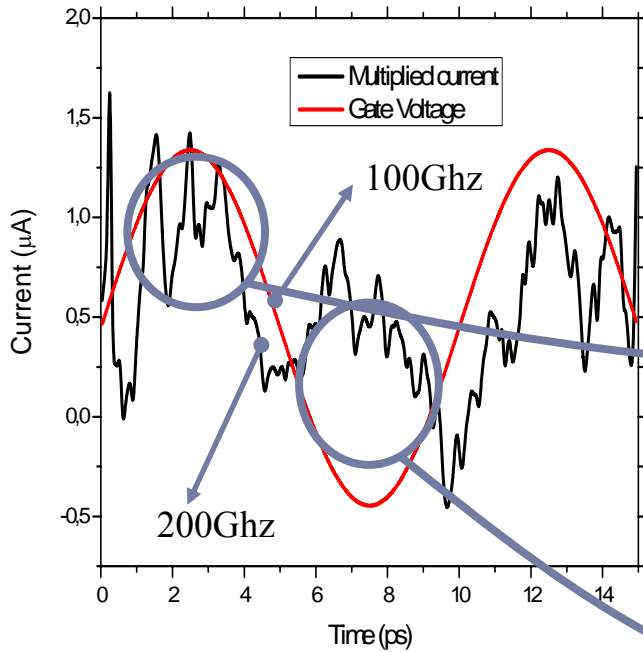
DTD parameters:

Barriers: 1.5nm, 0.6eV

Quantum well: 2.4nm.

Gate frequency: 250 GHz

4.2.- DTD Applications: THz harmonic generator

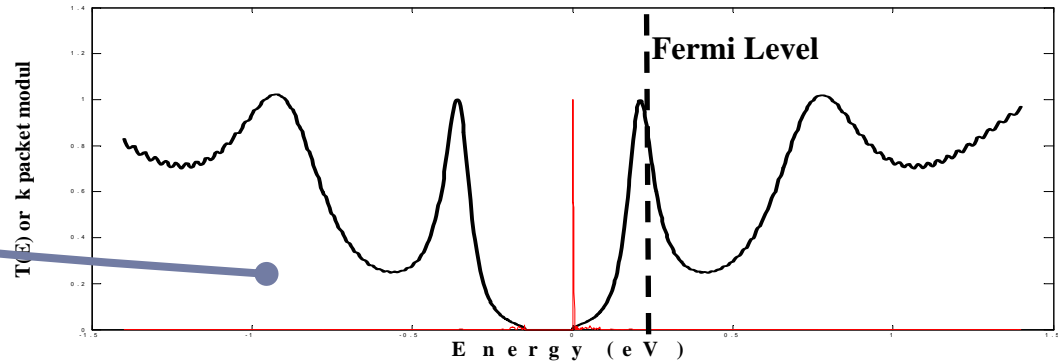


DTD parameters:

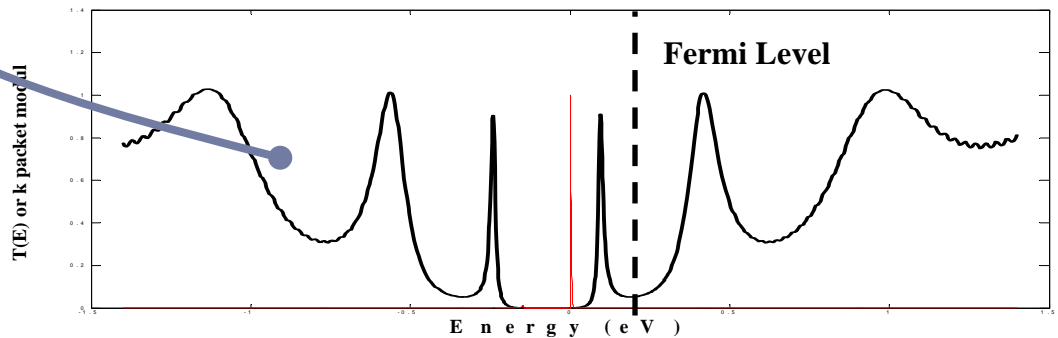
Barriers: 1.5nm, 0.8eV
Quantum well: 5.1 nm.
Gate frequency: 100 GHz



“Qualitative” explanation: Two resonances






“Qualitative” explanation: One resonance





5. Conclusions

Theoretical development:

-  We have presented a novel approach for the self-consistent simulation of the time-dependent total current at the range of THz.
-  The self-consistent solution of the 3D Poisson and Schrödinger equations are achieved using Bohm trajectories.
-  Computation of the time-dependent total current using quantum version of the Ramo-Shockley theorem.

THz applications:

-  Driven Tunneling Devices: Geometry and Operation.
-  This numerical approach is applied for the computing of tunneling currents in two different DTD configuration: Rectifier and a harmonic generator.

